

Cool MOS™ Power Transistor



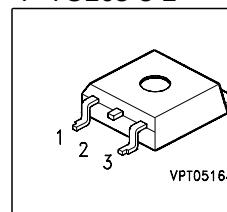
Feature

- New revolutionary high voltage technology
- Worldwide best $R_{DS(on)}$ in TO 220
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved noise immunity

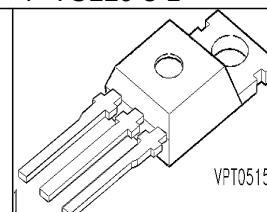
Product Summary

V_{DS}	600	V
$R_{DS(on)}$	0.19	Ω
I_D	20	A

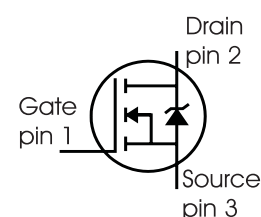
P-TO263-3-2



P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP20N60C2	P-TO220-3-1	Q67040-S4320	20N60C2
SPB20N60C2	P-TO263-3-2	Q67040-S4322	20N60C2



Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D	20	A
$T_C = 25\text{ °C}$			
$T_C = 100\text{ °C}$		13	
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\text{ puls}}$	40	
Avalanche energy, single pulse	E_{AS}	690	mJ
$I_D = 10\text{ A}$, $V_{DD} = 50\text{ V}$			
Avalanche energy, repetitive t_{AR} limited by $T_{jmax}^{1)}$	E_{AR}	1	
$I_D = 20\text{ A}$, $V_{DD} = 50\text{ V}$			
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	20	A
Reverse diode dv/dt	dv/dt	6	V/ns
$I_S = 20\text{ A}$, $V_{DS} < V_{DD}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_{jmax} = 150\text{ °C}$			
Gate source voltage	V_{GS}	± 20	V
Power dissipation	P_{tot}	208	W
$T_C = 25\text{ °C}$			
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	0.6	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ²⁾	R_{thJA}	- -	- 35	62 -	
Linear derating factor		-	-	1.67	W/K
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Static Characteristics

Drain-source breakdown voltage $V_{GS}=0V$, $I_D=0.25mA$	$V_{(BR)DSS}$	600	-	-	V
Drain-source avalanche breakdown voltage $V_{GS}=0V$, $I_D=20A$	$V_{(BR)DS}$	-	700	-	
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=1mA$	$V_{GS(th)}$	3.5	4.5	5.5	
Zero gate voltage drain current $V_{DS} = 600V$, $V_{GS} = 0V$, $T_j = 25\text{ °C}$ $V_{DS} = 600V$, $V_{GS} = 0V$, $T_j = 150\text{ °C}$	I_{DSS}	- -	0.1 -	1 100	μA
Gate-source leakage current $V_{GS}=20V$, $V_{DS}=0V$	I_{GSS}	-	-	100	
Drain-source on-state resistance $V_{GS}=10V$, $I_D=13A$, $T_j=25\text{ °C}$ $V_{GS}=10V$, $I_D=20A$, $T_j=150\text{ °C}$	$R_{DS(on)}$	- -	0.16 0.54	0.19 0.64	Ω
Gate input resistance $f = 1\text{ MHz}$, open drain	R_G	-	0.54	-	

¹Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

²Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics , at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 13\text{A}$	-	12	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	3000	-	pF
Output capacitance	C_{oss}		-	1170	-	
Reverse transfer capacitance	C_{rss}		-	28	-	
Effective output capacitance, ¹⁾ energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$ to 480V	-	83	-	pF
Effective output capacitance, ²⁾ time related	$C_{o(tr)}$		-	160	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 380\text{V}$, $V_{GS} = 0/13\text{V}$, $I_D = 20\text{A}$, $R_G = 3.6\Omega$, $T_j = 125^{\circ}\text{C}$	-	52	-	ns
Rise time	t_r		-	21	-	
Turn-off delay time	$t_{d(off)}$		-	56	84	
Fall time	t_f		-	6	9	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 350\text{V}$, $I_D = 20\text{A}$	-	21	-	nC
Gate to drain charge	Q_{gd}		-	46	-	
Gate charge total	Q_g	$V_{DD} = 350\text{V}$, $I_D = 20\text{A}$, $V_{GS} = 0$ to 10V	-	79	103	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 350\text{V}$, $I_D = 20\text{A}$	-	8	-	V

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

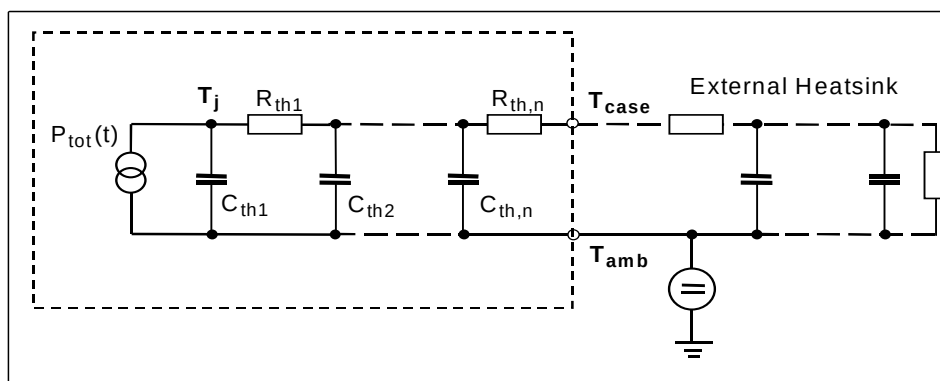
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Reverse Diode						
Inverse diode continuous forward current	I_S	$T_C=25^{\circ}\text{C}$	-	-	20	A
Inverse diode direct current, pulsed	I_{SM}		-	-	40	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=350\text{V}, I_F=I_S,$ $di_F/dt=100\text{A}/\mu\text{s}$	-	610	1040	ns
Reverse recovery charge	Q_{rr}		-	12	-	μC
Peak reverse recovery current	I_{rrm}		-	48	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	1500	-	$\text{A}/\mu\text{s}$

Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	

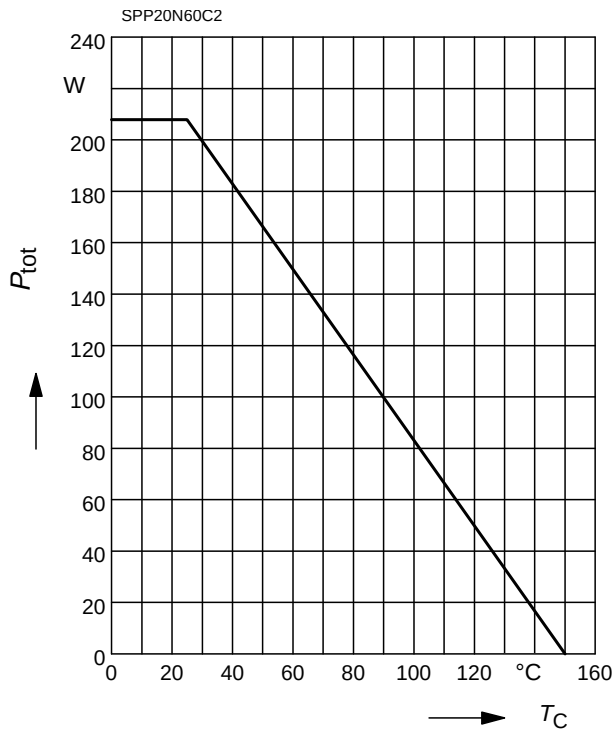
Transient thermal impedance

Thermal resistance			Thermal capacitance		
R_{th1}	0.007416	K/W	C_{th1}	0.0004409	Ws/K
R_{th2}	0.016		C_{th2}	0.001462	
R_{th3}	0.021		C_{th3}	0.0024	
R_{th4}	0.06		C_{th4}	0.003031	
R_{th5}	0.083		C_{th5}	0.02	
R_{th6}	0.038		C_{th6}	0.146	



1 Power dissipation

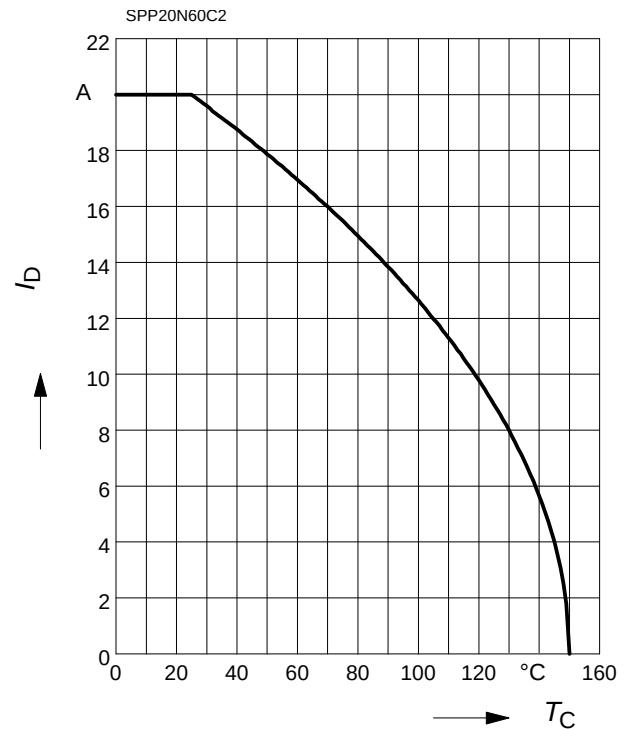
$$P_{\text{tot}} = f(T_C)$$



2 Drain current

$$I_D = f(T_C)$$

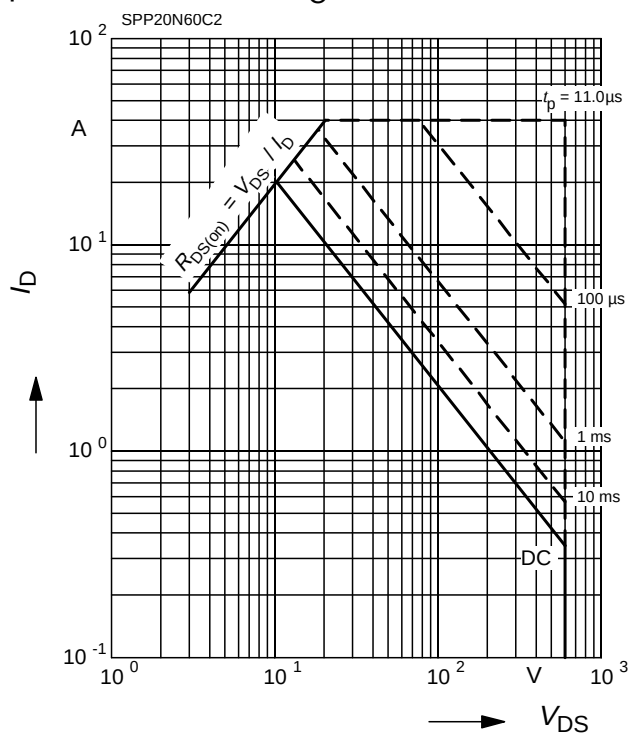
parameter: $V_{GS} \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

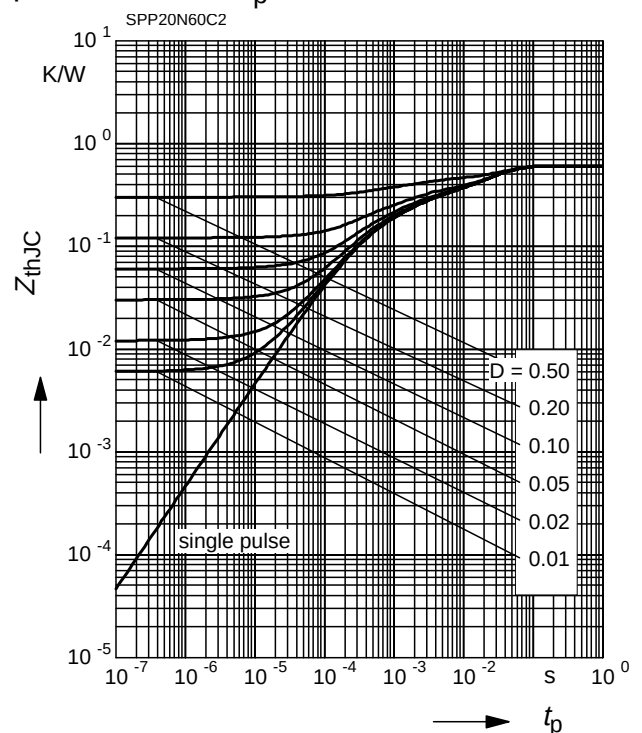
parameter: $D = 0$, $T_C = 25^\circ\text{C}$



4 Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

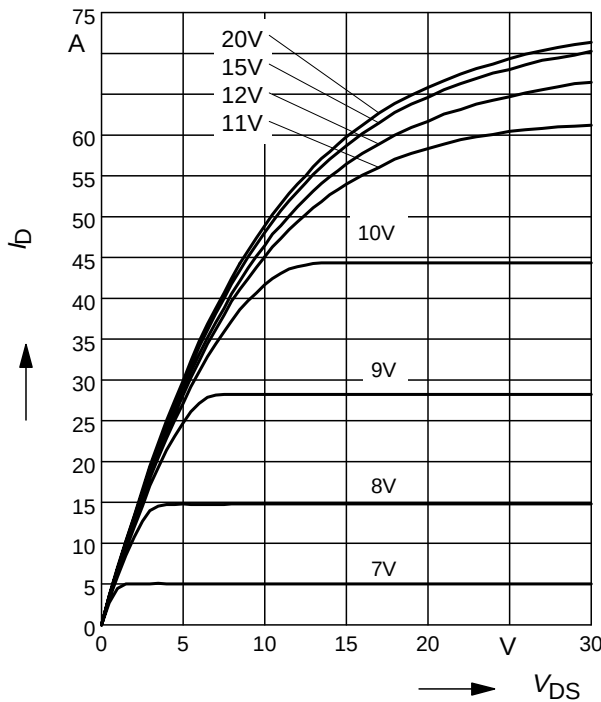
parameter: $D = t_p / T$



5 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

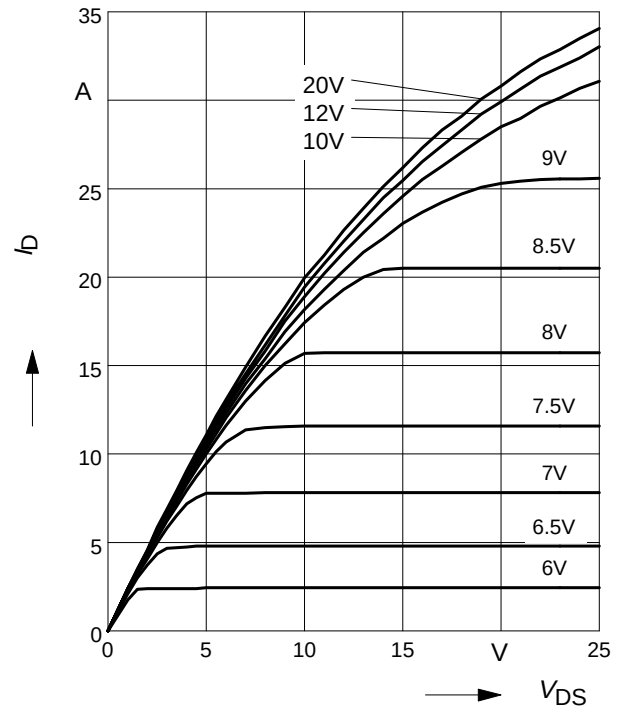
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



6 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

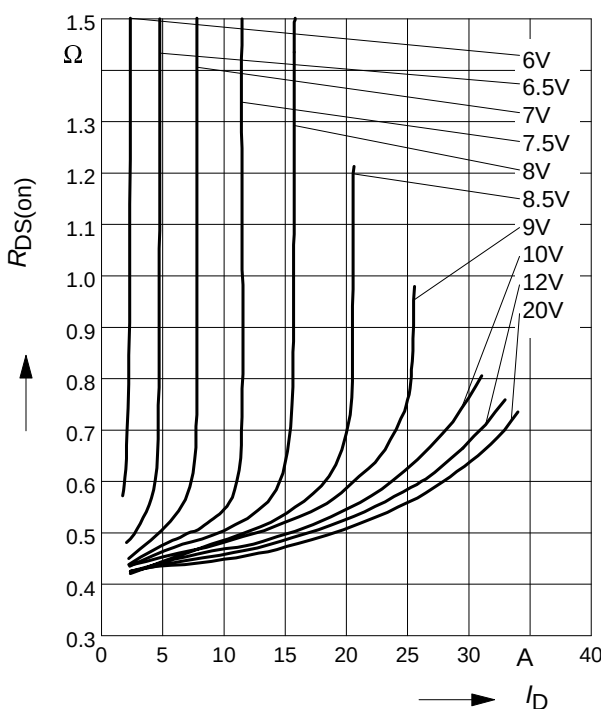
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



7 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

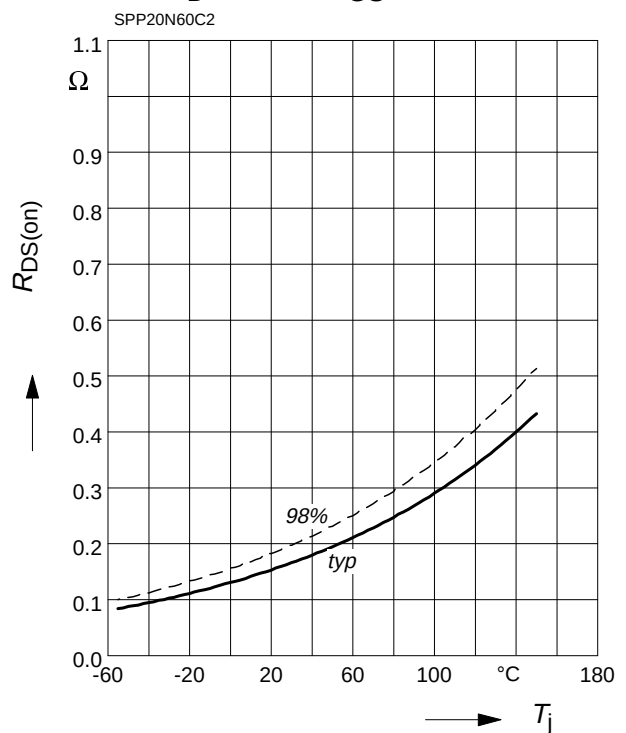
parameter: $T_j = 150^\circ\text{C}$, V_{GS}



8 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

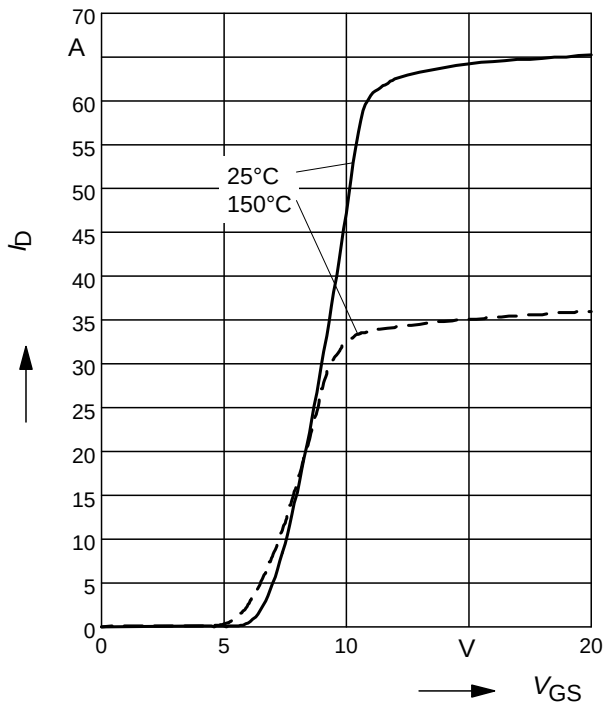
parameter: $I_D = 13 \text{ A}$, $V_{GS} = 10 \text{ V}$



9 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

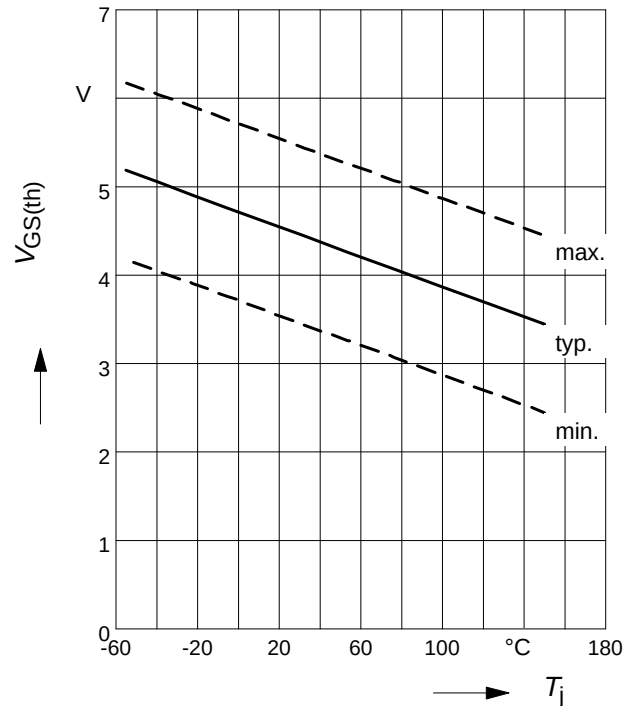
parameter: $t_p = 10 \mu s$



10 Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

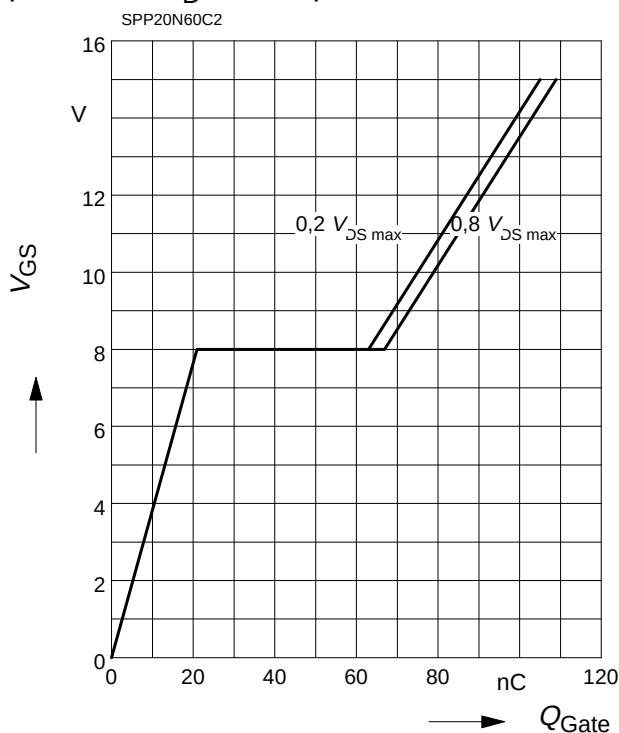
parameter: $V_{GS} = V_{DS}$, $I_D = 1$ mA



11 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

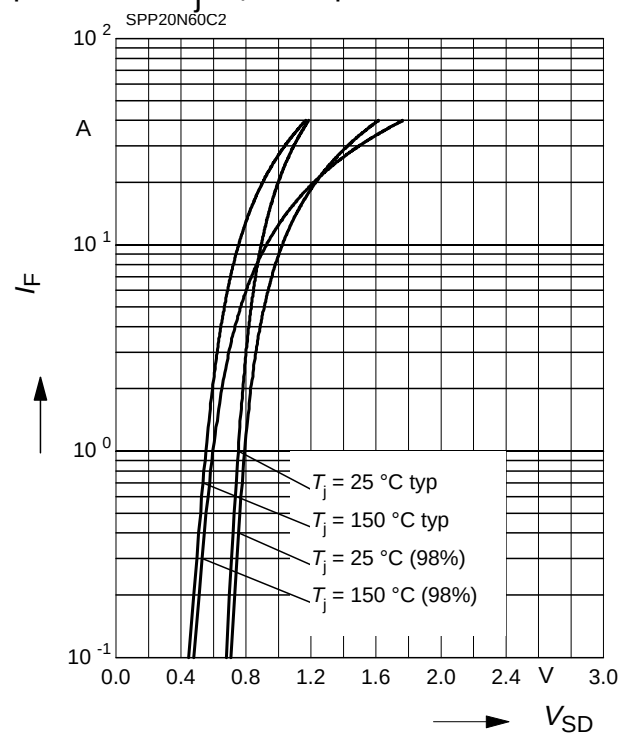
parameter: $I_D = 20$ A pulsed



12 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

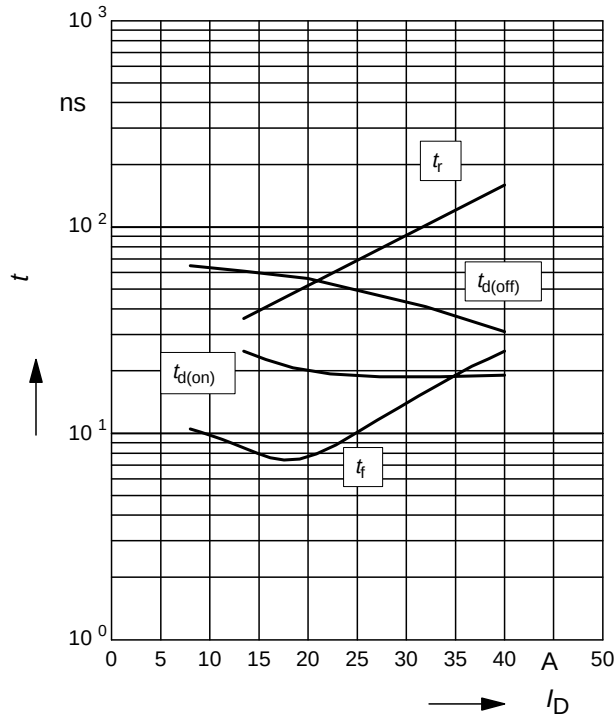
parameter: T_j , $t_p = 10 \mu s$



13 Typ. switching time

$t = f(I_D)$, inductive load, $T_j=125^\circ\text{C}$

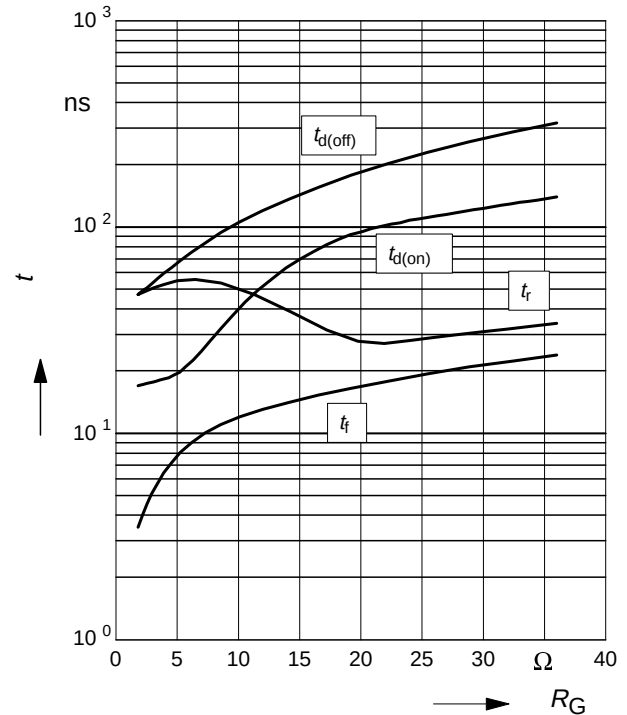
par.: $V_{DS}=380\text{V}$, $V_{GS}=0/+13\text{V}$, $R_G=3.6\Omega$



14 Typ. switching time

$t = f(R_G)$, inductive load, $T_j=125^\circ\text{C}$

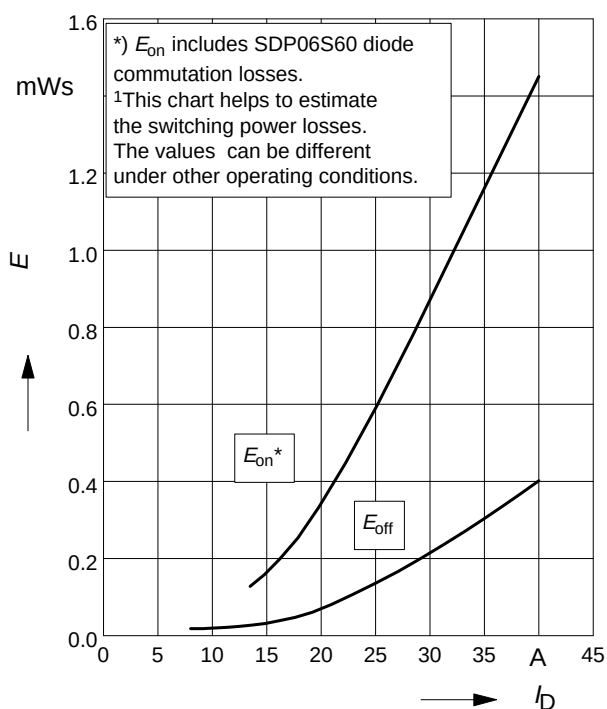
par.: $V_{DS}=380\text{V}$, $V_{GS}=0/+13\text{V}$, $I_D=20\text{A}$



15 Typ. switching losses¹⁾

$E = f(I_D)$, inductive load, $T_j=125^\circ\text{C}$

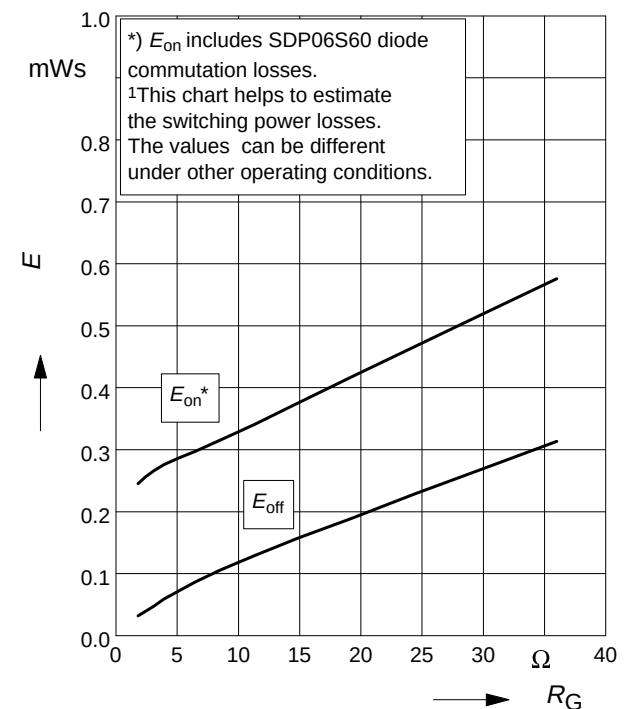
par.: $V_{DS}=380\text{V}$, $V_{GS}=0/+13\text{V}$, $R_G=3.6\Omega$



16 Typ. switching losses¹⁾

$E = f(R_G)$, inductive load, $T_j=125^\circ\text{C}$

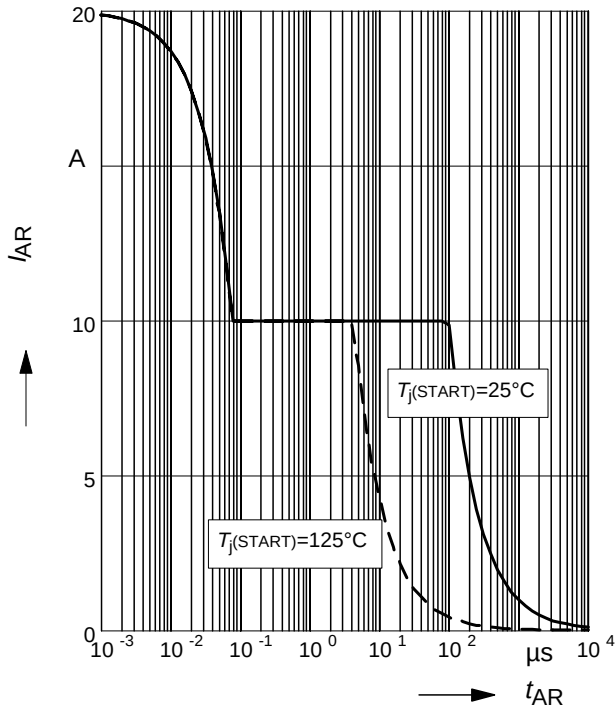
par.: $V_{DS}=380\text{V}$, $V_{GS}=0/+13\text{V}$, $I_D=20\text{A}$



17 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

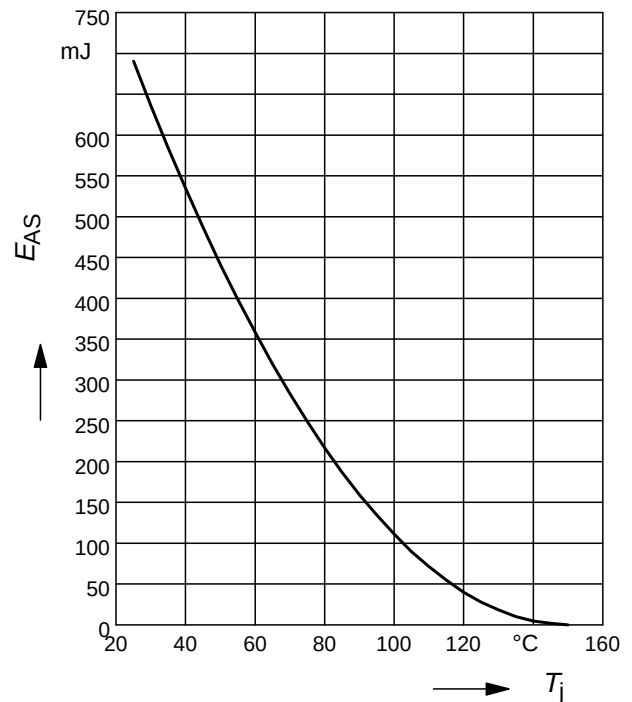
par.: $T_j \leq 150^\circ\text{C}$



18 Avalanche energy

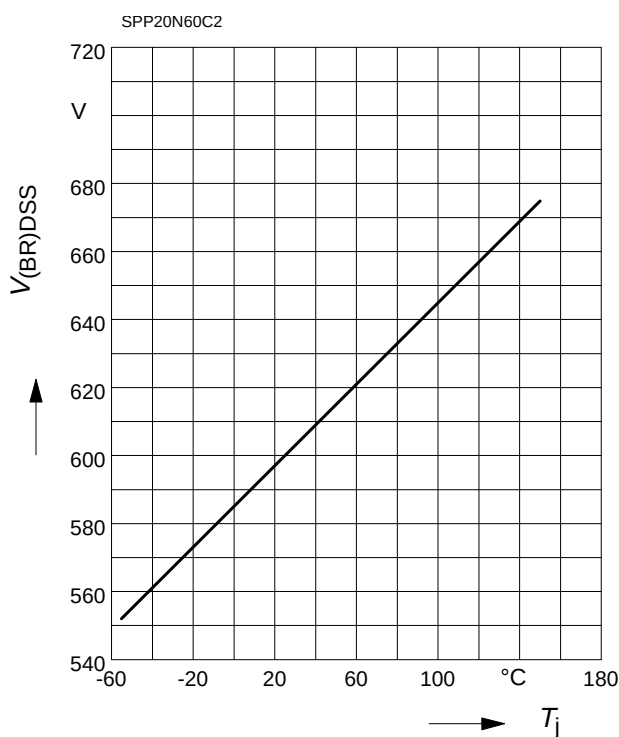
$$E_{AS} = f(T_j)$$

par.: $I_D = 10\text{ A}$, $V_{DD} = 50\text{ V}$



19 Drain-source breakdown voltage

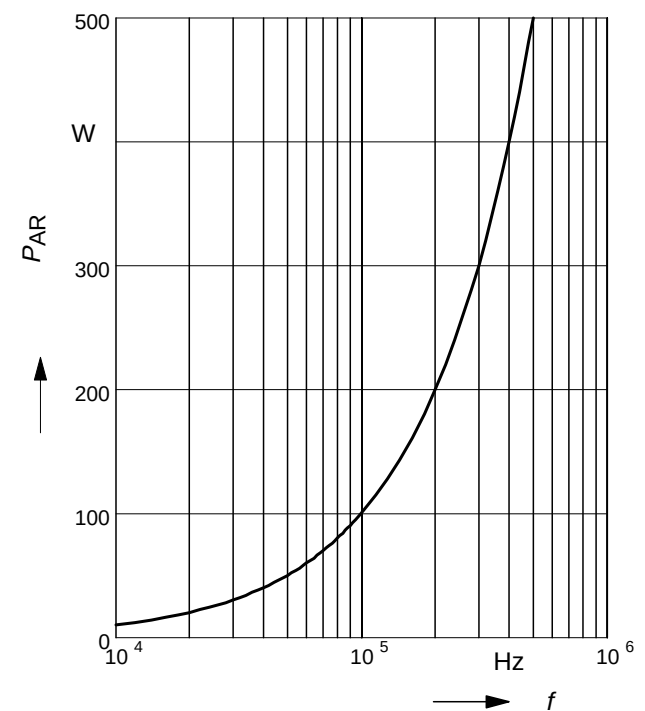
$$V_{(BR)DSS} = f(T_j)$$



20 Avalanche power losses

$$P_{AR} = f(f)$$

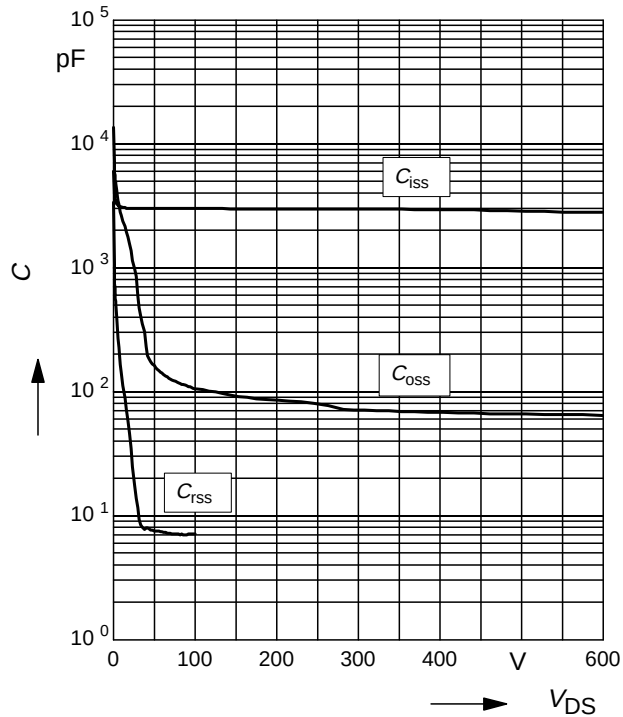
parameter: $E_{AR}=1\text{ mJ}$



21 Typ. capacitances

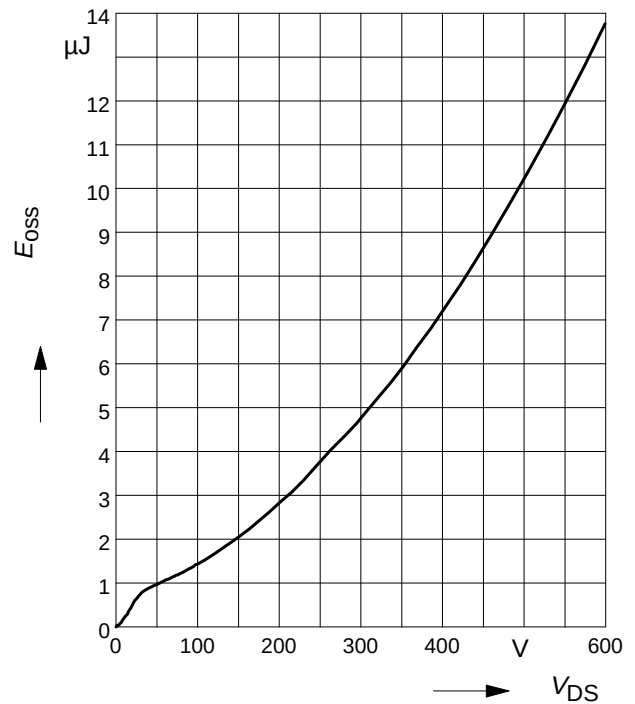
$$C = f(V_{DS})$$

parameter: $V_{GS}=0V$, $f=1\text{ MHz}$

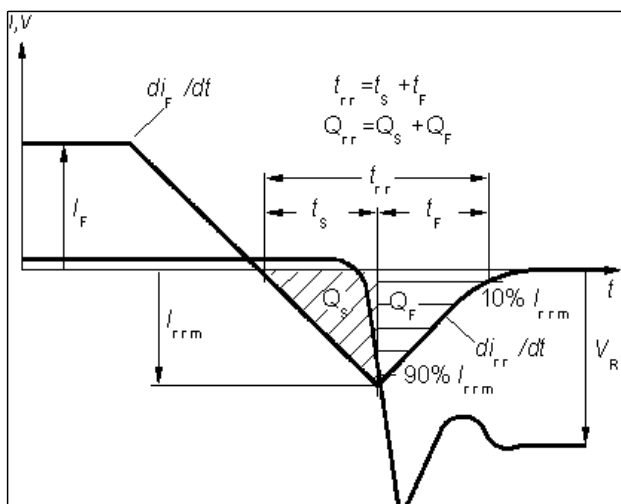


22 Typ. C_{oss} stored energy

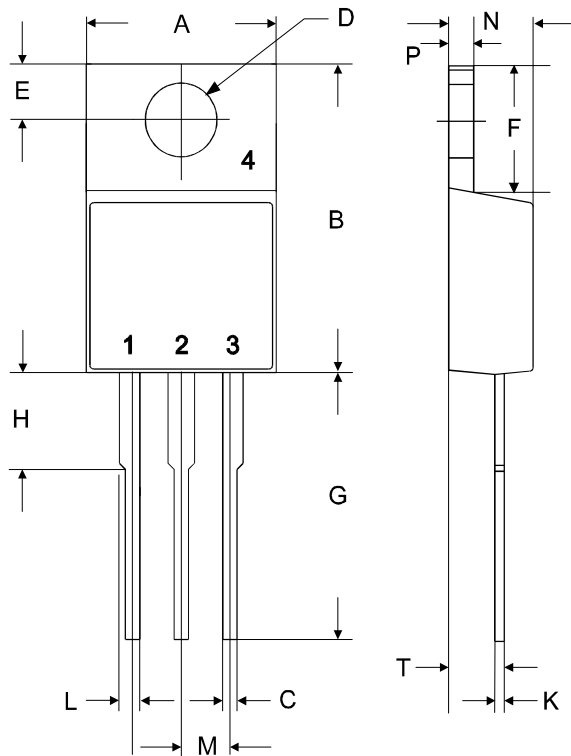
$$E_{oss} = f(V_{DS})$$



Definition of diodes switching characteristics

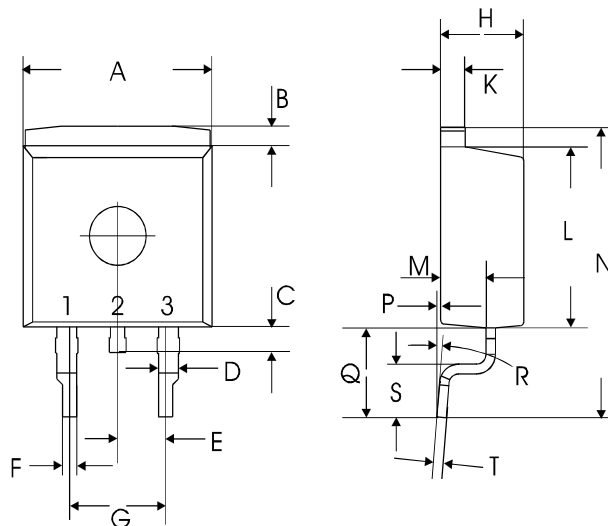


P-TO220-3-1

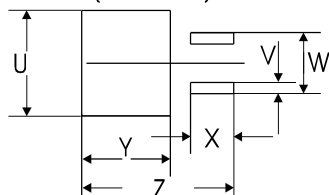


symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.70	10.30	0.3819	0.4055
B	14.88	15.95	0.5858	0.6280
C	0.65	0.86	0.0256	0.0339
D	3.55	3.89	0.1398	0.1531
E	2.60	3.00	0.1024	0.1181
F	6.00	6.80	0.2362	0.2677
G	13.00	14.00	0.5118	0.5512
H	4.35	4.75	0.1713	0.1870
K	0.38	0.65	0.0150	0.0256
L	0.95	1.32	0.0374	0.0520
M	2.54 typ.		0.1 typ.	
N	4.30	4.50	0.1693	0.1772
P	1.17	1.40	0.0461	0.0551
T	2.30	2.72	0.0906	0.1071

TO-263 (D²Pak/P-TO220SMD)



Footprint
(dif. scale)



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.80	10.20	0.3858	0.4016
B	0.70	1.30	0.0276	0.0512
C	1.00	1.60	0.0394	0.0630
D	1.03	1.07	0.0406	0.0421
E	2.54 typ.		0.1 typ.	
F	0.65	0.85	0.0256	0.0335
G	5.08 typ.		0.2 typ.	
H	4.30	4.50	0.1693	0.1772
K	1.17	1.37	0.0461	0.0539
L	9.05	9.45	0.3563	0.3720
M	2.30	2.50	0.0906	0.0984
N	15 typ.		0.5906 typ.	
P	0.00	0.20	0.0000	0.0079
Q	4.20	5.20	0.1654	0.2047
R	8° max		8° max	
S	2.40	3.00	0.0945	0.1181
T	0.40	0.60	0.0157	0.0236
U	10.80		0.4252	
V	1.15		0.0453	
W	6.23		0.2453	
X	4.60		0.1811	
Y	9.40		0.3701	
Z	16.15		0.6358	

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